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INFORMATION DISCLOSURE STATEMENT BY APPLICANT			Filing Date	FEBRUARY 19 2004			
			First Named Inventor				
			Group Art Unit	2823			
(use as many sheets as necessar	1		Examiner Name	W. DAVID COLUMAN			
Sheel 1	of	1	Attorney Docket Number	SC13265TP			

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<u>a</u>	AC	LANGDO et al., "Preparation of Novel SiGe-Free Strained Si on Insulator Substrates," AMBERWAVE SYSTEMS CORP., SALEM, NH, 2 pgs.					
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